High Speed Switching Silicon P-channel MOSFET

#### **DESCRIPTION**

INJ0512AC1 is a Silicon P-channel MOSFET.

This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

### **FEATURE**

- •Input impedance is high, and not necessary to consider a drive electric current.
- •High drain current ID=-4.6A
- •Drive voltage −4V
- \*Low on Resistance. RDS(ON)=36m  $\Omega$  typ(@VGS=-10V)  $RDS(ON)=47m\,\Omega\,typ(@VGS=-4.5V)$
- · High speed switching.

#### **APPLICATION**

High speed switching, Analog switching

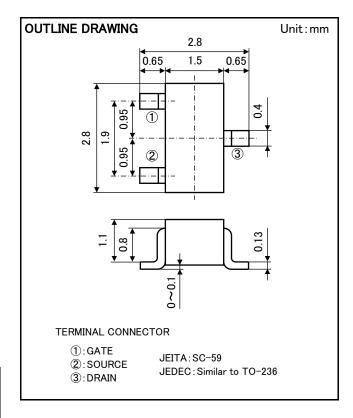
## MAXIMUM RATINGS (Ta=25°C)

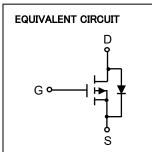
Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	VDSS	-30	V	
Gate-Source Voltage	Vgss	±20	V	
Drain Current(DC) (%1)	ĪD	-4.6	Α	
Drain Current(Pulse) (%2)	ĪDP	-25	Α	
Total Power Dissipation (%1)	Pb	0.9	W	
Channel Temperature	Tch	+150	°C	
Storage Temperature	Tstg	−55 <b>~</b> +150	°C	

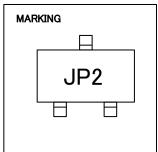
X1 package mounted on glass-epoxy substrate.

 $(39\text{mm} \times 39\text{mm} \times 1.6\text{mm},\text{Cu pad }1500\text{mm}^2)$ 

 $32 \text{ Pw} \le 1 \text{ms}$  , Duty cycle  $\le 1\%$ 





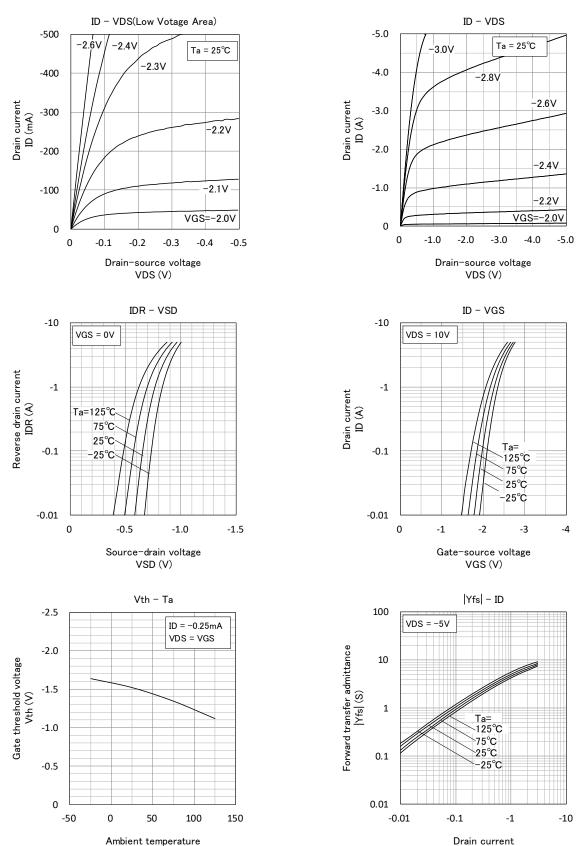


### ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit	
			MIN	TYP	MAX	Unit	
Drain-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30	_	-	٧	
Gate-Source Leak Current	Igss	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	_	-	±1.0	μА	
Zero Gate Voltage Drain Current	<b>I</b> DSS	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	_	-	-1.0		
Gate Threshold Voltage	Vth	$I_D$ =-250 $\mu$ A, $V_{DS}$ = $V_{GS}$	-1.0	-	-2.5	٧	
Static Drain-Source On-State Resistance	Rds(on)	I <sub>D</sub> =-4.6A, V <sub>GS</sub> =-4.5V	-	47	55	mΩ	
		I <sub>D</sub> =-4.6A, V <sub>GS</sub> =-10V	-	36	41	111.75	
Input Capacitance	Ciss		-	750	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1MHz	_	130	_		
Feedback Capacitance	Crss		-	100	-		
Switching Time	ton	\( - 20\( \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	40	-	ns	
	toff	$V_{DD}$ =-20V, $I_{D}$ =-200mA, $V_{GS}$ =-5V	_	160	_		

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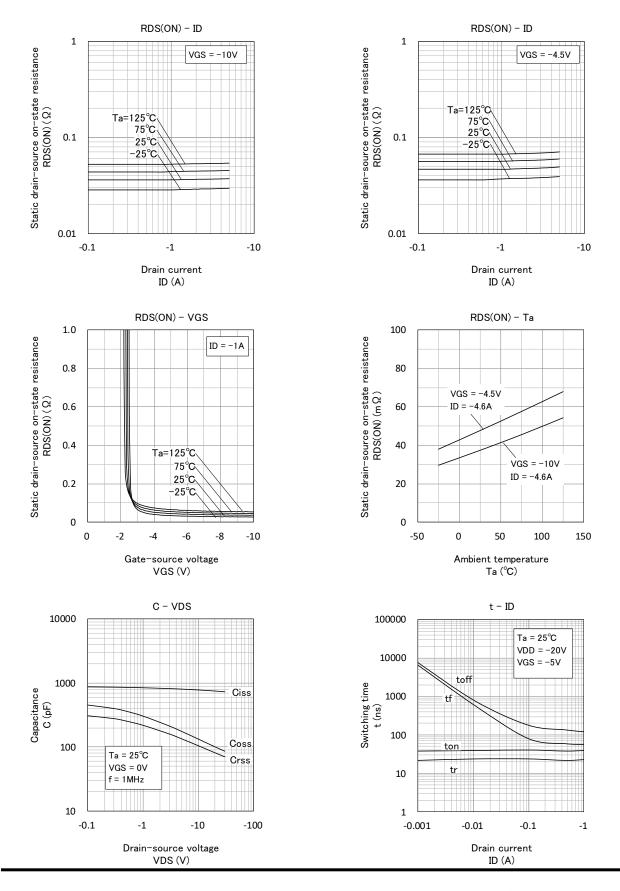
### TYPICAL CHARACTERISTICS



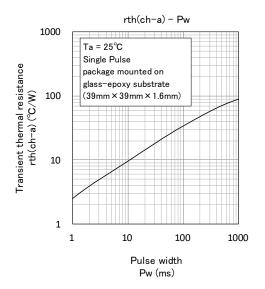
ID (A)

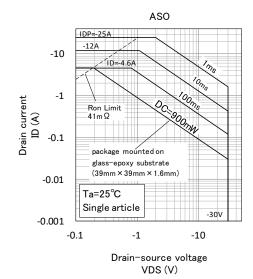
Ta (°C)

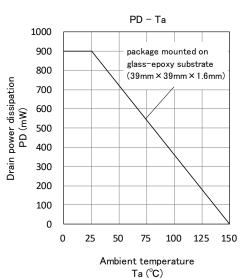
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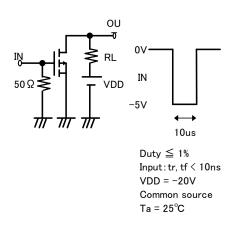
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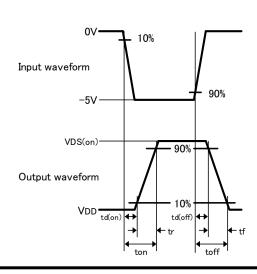






### Switching time test condition





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